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FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
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10/685,064

Applicant

Peter Weitz

Filing Date
October 14, 2003

Group Art Unit

2823

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
K.N.	A	6,211,559 B1	04/03/03	Zhu et al.			
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
K.N.	J	1 061 592 A2	12/20/00	Europe			X
K.N.	K	99/14760	03/25/99	WIPO			X
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

K.N.	O	Roy E. Scheuerlein: "Magneto-Resistive IC Memory Limitations and Architecture Implications", <i>Proceedings of the 7th IEEE International Nonvolatile Memory Technology Conference</i> , June 22-24, 1998, pp. 47-50
K.N.	P	S. Tehrani et al.: "Recent Developments in Magnetic Tunnel Junction MRAM", <i>IEEE Transactions on Magnetics</i> , Vol. 36, No. 5, September 2000, pp. 2752-2757

EXAMINER

K. R. M. /

DATE CONSIDERED

07/11/04

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.